
2SB649, 2SB649A

Silicon PNP Epitaxial

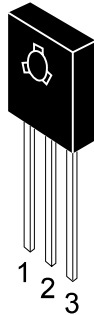
HITACHI

Application

Low frequency power amplifier complementary pair with 2SD669/A

Outline

TO-126 MOD



1. Emitter
2. Collector
3. Base

2SB649, 2SB649A

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SB649	2SB649A	
Collector to base voltage	V_{CBO}	-180	-180	V
Collector to emitter voltage	V_{CEO}	-120	-160	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-1.5	-1.5	A
Collector peak current	$I_{C(peak)}$	-3	-3	A
Collector power dissipation	P_C	1	1	W
	P_C^{*1}	20	20	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$